



TO-92 Plastic-Encapsulate Transistors

BC212, B, C TRANSISTOR (PNP)

FEATURES

Power dissipation

P_{CM} : 0.35 W ($T_{amb}=25^{\circ}C$)

Collector current

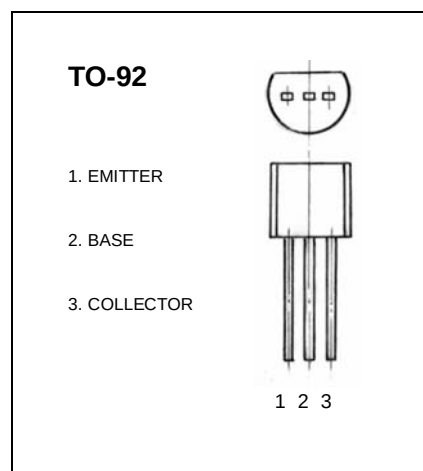
I_{CM} : -0.1 A

Collector-base voltage

$V_{(BR)CBO}$: -60 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-10\mu A, I_E=0$	-60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-2mA, I_B=0$	-50		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu A, I_C=0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB}=-30V, I_E=0$		-15	nA
Collector cut-off current	I_{CEO}	$V_{CE}=-30V, I_B=0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-4V, I_C=0$		-15	nA
DC current gain BC212 BC212B BC212C	$h_{FE(1)}$	$V_{CE}=-5V, I_C=-2mA$	140 140 350	600 400 600	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-100mA, I_B=-5mA$		-0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-100mA, I_B=-5mA$		-1.2	V
Transition frequency	f_T	$V_{CE}=-5V, I_C=-10mA$ $f=100MHz$	200		MHz